



# **DNBT8105**

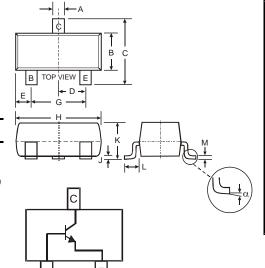
#### 1A NPN SURFACE MOUNT TRANSISTOR

#### **Features**

- **Epitaxial Planar Die Construction**
- Ideal for Low Power Amplification and Switching
- High Collector Current Rating
- Complementary Version Available (DPBT8105)
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green Device" (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: K81, See Page 3
- Ordering & Date Code Information: See Page 3
- Weight: 0.008 grams (approximate)



SOT-23									
Dim	Min	Max							
Α	0.37	0.51							
В	1.20	1.40							
С	2.30	2.50							
D	0.89	1.03							
E	0.45	0.60							
G	1.78	2.05							
H	2.80	3.00							
7	0.013	0.10							
K	0.903	1.10							
L	0.45	0.61							
М	0.085	0.180							
α	0°	8°							
All Dimensions in mm									

### **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	80	V
Collector-Emitter Voltage	V <sub>CEO</sub>	60	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current - Continuous	Ic	1	Α
Peak Pulse Collector Current	I <sub>CM</sub>	2	Α

Top View

### **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1) @ T <sub>A</sub> = 25°C	P <sub>D</sub>	600	mW
Thermal Resistance, Junction to Ambient (Note 1) @ T <sub>A</sub> = 25°C	$R_{ hetaJA}$	209	°C/W
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

- Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- No purposefully added lead.
- 3. Diode's Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.



### **Electrical Characteristics** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)	-				
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	80		V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	60	_	V	$I_C = 10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5	_	V	$I_E = 100 \mu A, I_C = 0$
Collector Cutoff Current	I <sub>CBO</sub>		100	nA	$V_{CB} = 60V, I_{E} = 0$
Collector Cutoff Current	I <sub>CES</sub>		100	nA	V <sub>CES</sub> = 60V
Emitter Cutoff Current	I <sub>EBO</sub>		100	nA	$V_{EB} = 4V, I_{C} = 0$
ON CHARACTERISTICS (Note 4)					
DC Current Gain	h <sub>FE</sub>	100 100 80 30	300 — —	٧	$I_C = 1mA$ , $V_{CE} = 5V$ $I_C = 500mA$ , $V_{CE} = 5V$ $I_C = 1A$ , $V_{CE} = 5V$ $I_C = 2A$ , $V_{CE} = 5V$
Collector-Emitter Saturation Voltage		_	0.25 0.5	V	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$ $I_C = 1 \text{A}, I_B = 100 \text{mA}$
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>		1.1	V	I <sub>C</sub> = 1A, I <sub>B</sub> = 100mA
Base-Emitter Turn On Voltage	V <sub>BE(ON)</sub>		1.0	V	$I_{C} = 1A, V_{CE} = 5V$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	Cobo		10	pF	V <sub>CB</sub> = 10V, f = 1.0MHz
Current Gain-Bandwidth Product	f <sub>T</sub>	150	_	MHz	$V_{CE} = 10V$ , $I_{C} = 50mA$ , $f = 100MHz$

Notes: 4. Short duration pulse test used to minimize self-heating effect.

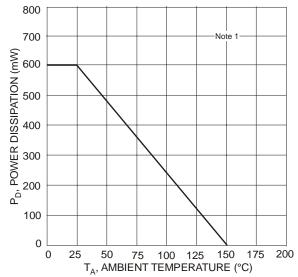


Fig. 1, Max Power Dissipation vs. Ambient Temperature

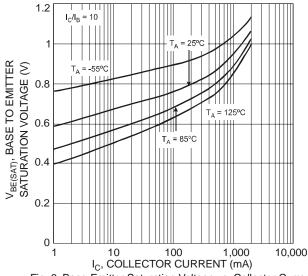


Fig. 3, Base-Emitter Saturation Voltage vs. Collector Current

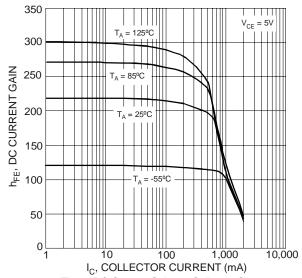


Fig. 2, DC Current Gain vs. Collector Current

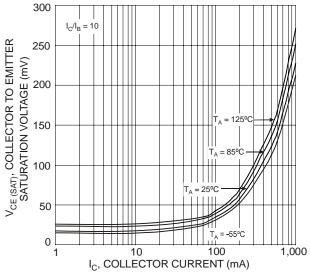


Fig. 4, Collector-Emitter Saturation Voltage vs. Collector Current



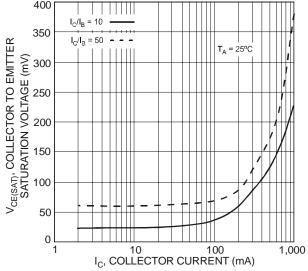


Fig. 5, Collector-Emitter Saturation Voltage vs. Collector Current

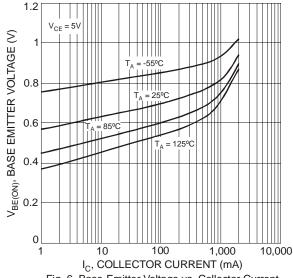


Fig. 6, Base-Emitter Voltage vs. Collector Current

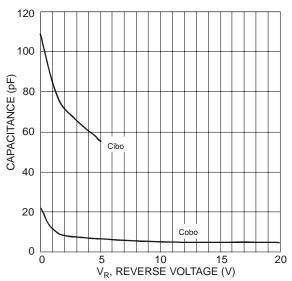


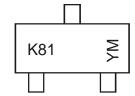
Fig. 7, Capacitance vs. Reverse Voltage

## Ordering Information (Note 5)

Device	Packaging	Shipping		
DNBT8105-7	SOT-23	3000/Tape & Reel		

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

# **Marking Information**



K81 = Product Type Marking Code YM = Date Code Marking Y = Year ex: S = 2005 M = Month ex: 9 = September

Date Code Key									
Year	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	R	S	Т	U	V	W	Χ	Υ	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



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